

Test Laboratory: HUAWEI SAR Lab

**HAC\_ER3DV6\_M570-CDMA800-1013CH****DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 824.7 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 11/11/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn852; Calibrated: 11/16/2011
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1):** Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 71.5 V/m

Probe Modulation Factor = 1.05

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 87.5 V/m; Power Drift = -0.00442 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak E-field in V/m

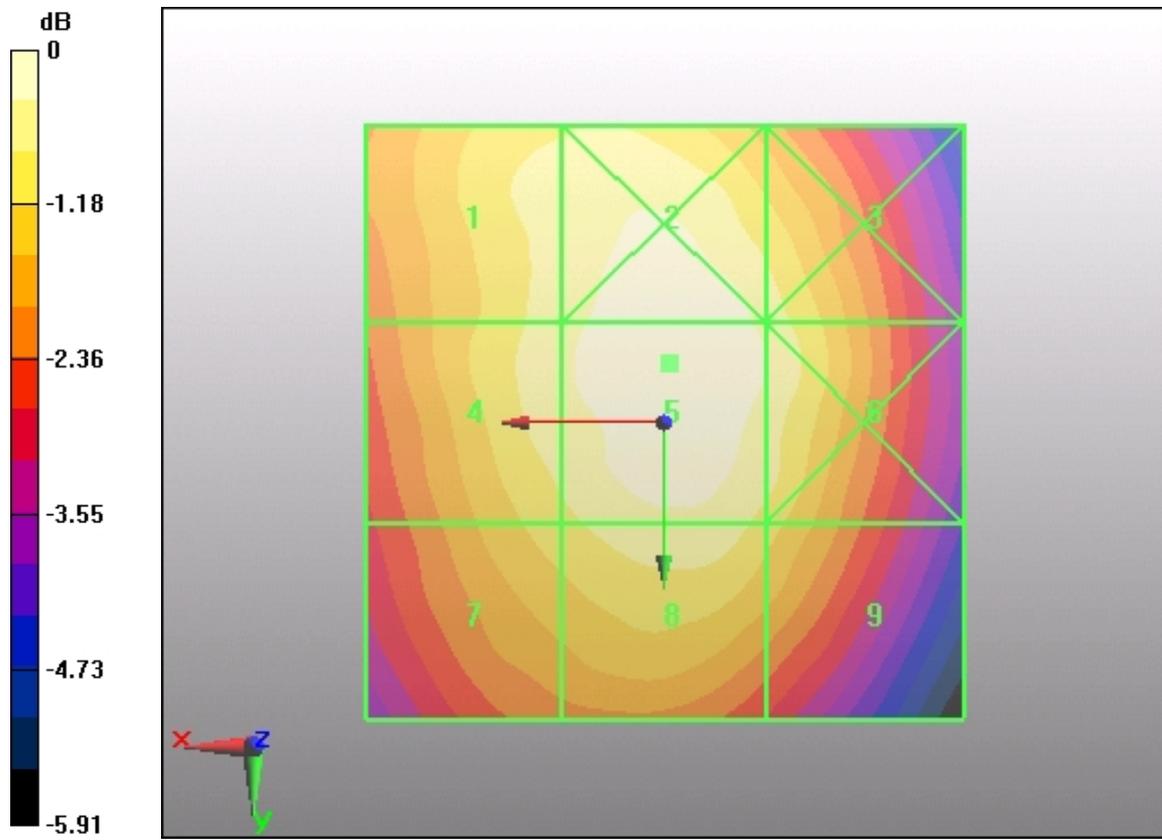
Grid 1 <b>67.2 M4</b>	Grid 2 <b>70.7 M4</b>	Grid 3 <b>67.4 M4</b>
Grid 4 <b>67.6 M4</b>	Grid 5 <b>71.5 M4</b>	Grid 6 <b>68.5 M4</b>
Grid 7 <b>64.4 M4</b>	Grid 8 <b>67.6 M4</b>	Grid 9 <b>64 M4</b>

**Cursor:**

Total = 71.5 V/m

E Category: M4

Location: -0.5, -5, 8.7 mm



0 dB = 71.5V/m

Test Laboratory: HUAWEI SAR Lab

**HAC\_ER3DV6\_M570-CDMA800-384CH****DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 836.52 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 11/11/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn852; Calibrated: 11/16/2011
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1):** Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 64.3 V/m

Probe Modulation Factor = 1.05

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 78.9 V/m; Power Drift = -0.112 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak E-field in V/m

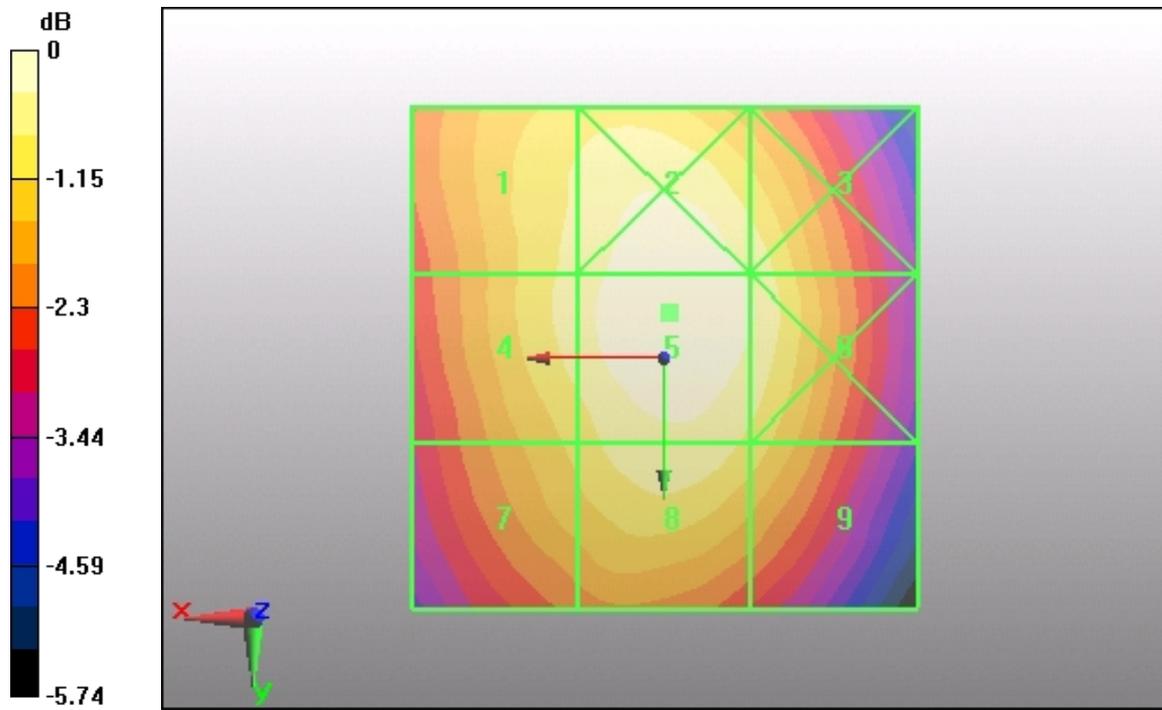
Grid 1 <b>60.1 M4</b>	Grid 2 <b>63.4 M4</b>	Grid 3 <b>61.2 M4</b>
Grid 4 <b>60.5 M4</b>	Grid 5 <b>64.3 M4</b>	Grid 6 <b>61.9 M4</b>
Grid 7 <b>57.3 M4</b>	Grid 8 <b>61 M4</b>	Grid 9 <b>58.1 M4</b>

**Cursor:**

Total = 64.3 V/m

E Category: M4

Location: -0.5, -4.5, 8.7 mm



0 dB = 64.3V/m

Test Laboratory: HUAWEI SAR Lab

**HAC\_ER3DV6\_M570-CDMA800-777CH****DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 848.31 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 11/11/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn852; Calibrated: 11/16/2011
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1):** Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 74.2 V/m

Probe Modulation Factor = 1.05

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 92.6 V/m; Power Drift = -0.184 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak E-field in V/m

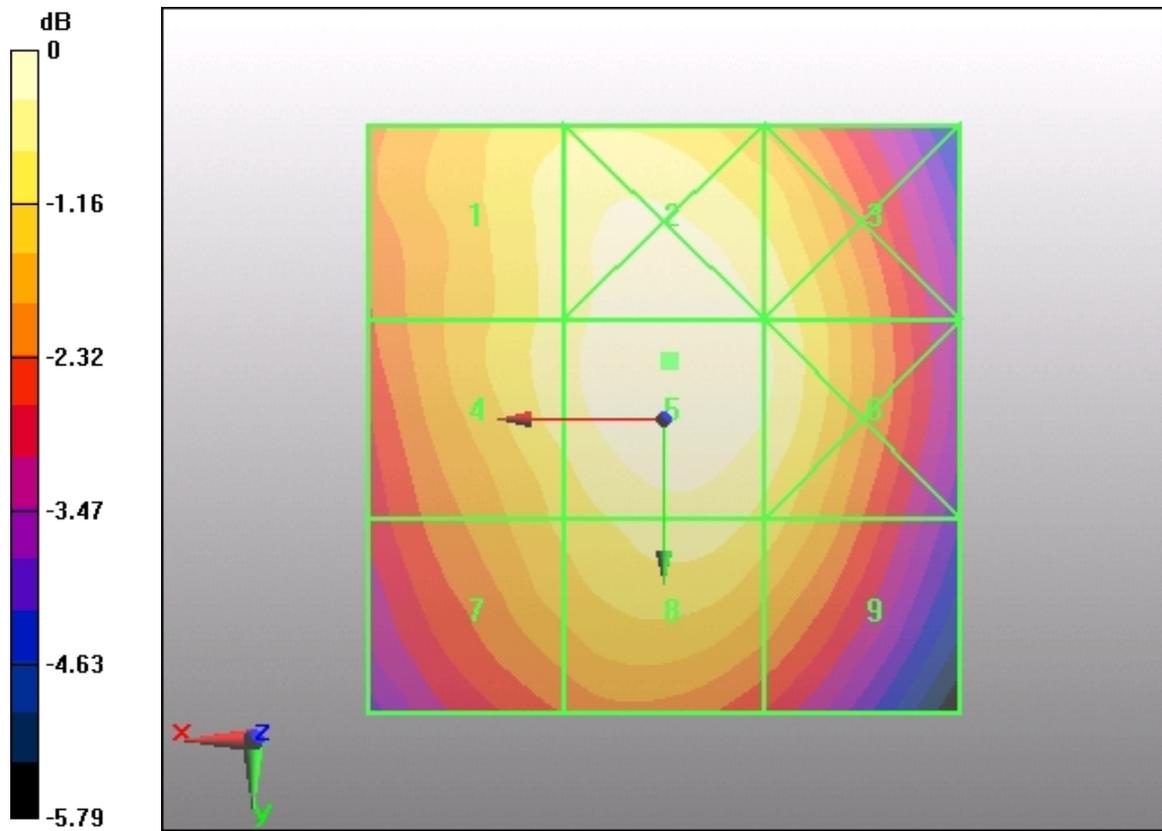
Grid 1 <b>69.5 M4</b>	Grid 2 <b>73.5 M4</b>	Grid 3 <b>70.8 M4</b>
Grid 4 <b>70 M4</b>	Grid 5 <b>74.2 M4</b>	Grid 6 <b>71.6 M4</b>
Grid 7 <b>65.7 M4</b>	Grid 8 <b>69.9 M4</b>	Grid 9 <b>66.8 M4</b>

**Cursor:**

Total = 74.2 V/m

E Category: M4

Location: -0.5, -5, 8.7 mm



0 dB = 74.2V/m

Test Laboratory: HUAWEI SAR Lab

## HAC\_ER3DV6\_M570-CDMA1700-25CH

**DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 1711.25 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 11/11/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn852; Calibrated: 11/16/2011
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

### Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 45.5 V/m

Probe Modulation Factor = 1.02

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 49.5 V/m; Power Drift = -0.078 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak E-field in V/m

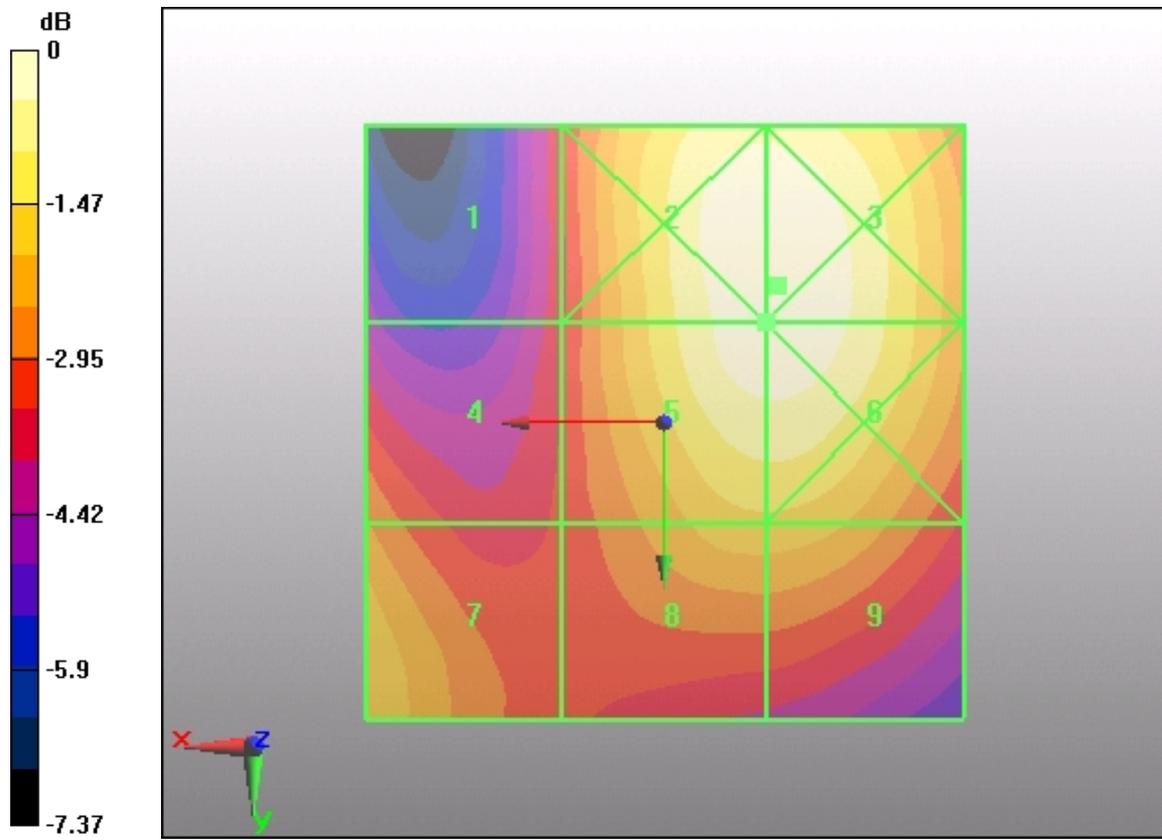
Grid 1 <b>31.1 M4</b>	Grid 2 <b>45.9 M4</b>	Grid 3 <b>46 M4</b>
Grid 4 <b>35.1 M4</b>	Grid 5 <b>45.5 M4</b>	Grid 6 <b>45.6 M4</b>
Grid 7 <b>39.1 M4</b>	Grid 8 <b>38.3 M4</b>	Grid 9 <b>38.2 M4</b>

#### Cursor:

Total = 46 V/m

E Category: M4

Location: -9.5, -11.5, 8.7 mm



0 dB = 46V/m

Test Laboratory: HUAWEI SAR Lab

**HAC\_ER3DV6\_M570-CDMA1700-450CH****DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 1732.5 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 11/11/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn852; Calibrated: 11/16/2011
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1):** Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 42.1 V/m

Probe Modulation Factor = 1.02

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 44.8 V/m; Power Drift = 0.058 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak E-field in V/m

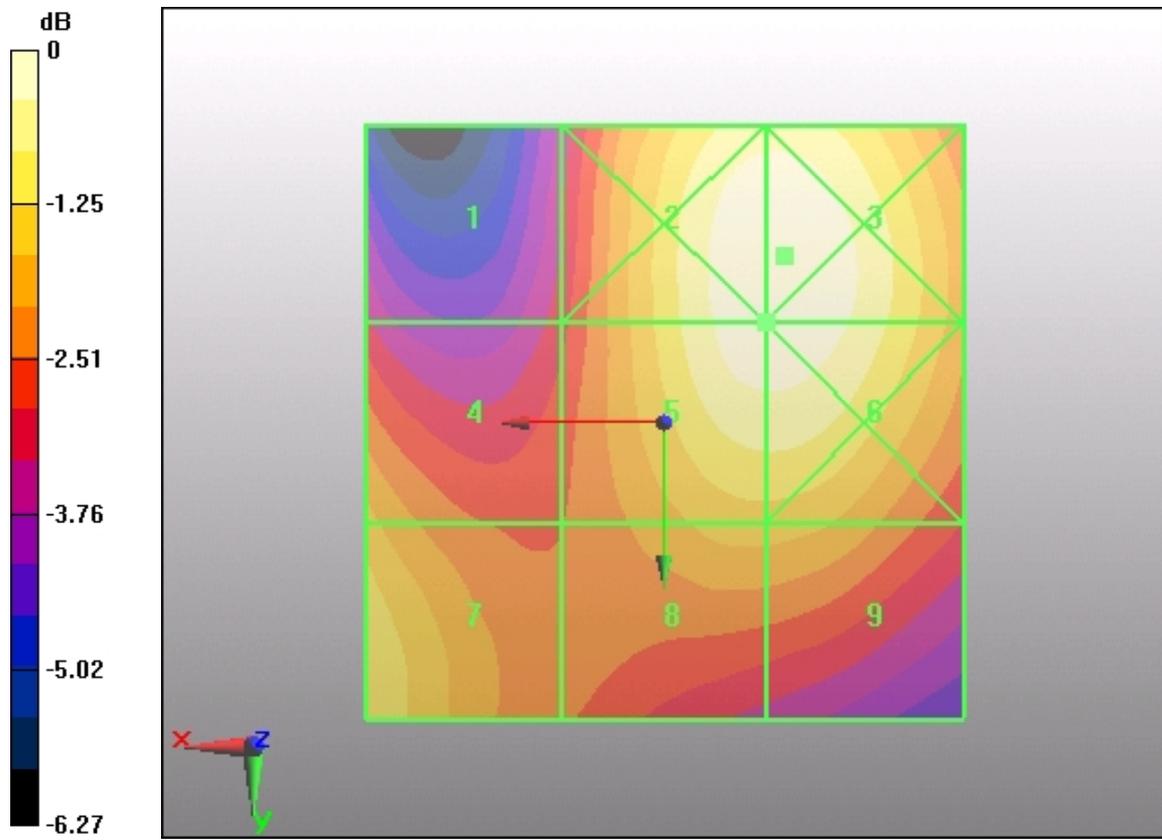
Grid 1 <b>30.1 M4</b>	Grid 2 <b>42.6 M4</b>	Grid 3 <b>42.7 M4</b>
Grid 4 <b>36.1 M4</b>	Grid 5 <b>42.1 M4</b>	Grid 6 <b>42.1 M4</b>
Grid 7 <b>39 M4</b>	Grid 8 <b>36.1 M4</b>	Grid 9 <b>36.1 M4</b>

**Cursor:**

Total = 42.7 V/m

E Category: M4

Location: -10, -14, 8.7 mm



0 dB = 42.7V/m

Test Laboratory: HUAWEI SAR Lab

**HAC\_ER3DV6\_M570-CDMA1700-850CH****DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 1752.5 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 11/11/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn852; Calibrated: 11/16/2011
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1):** Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 41.3 V/m

Probe Modulation Factor = 1.02

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 49.3 V/m; Power Drift = -0.078 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak E-field in V/m

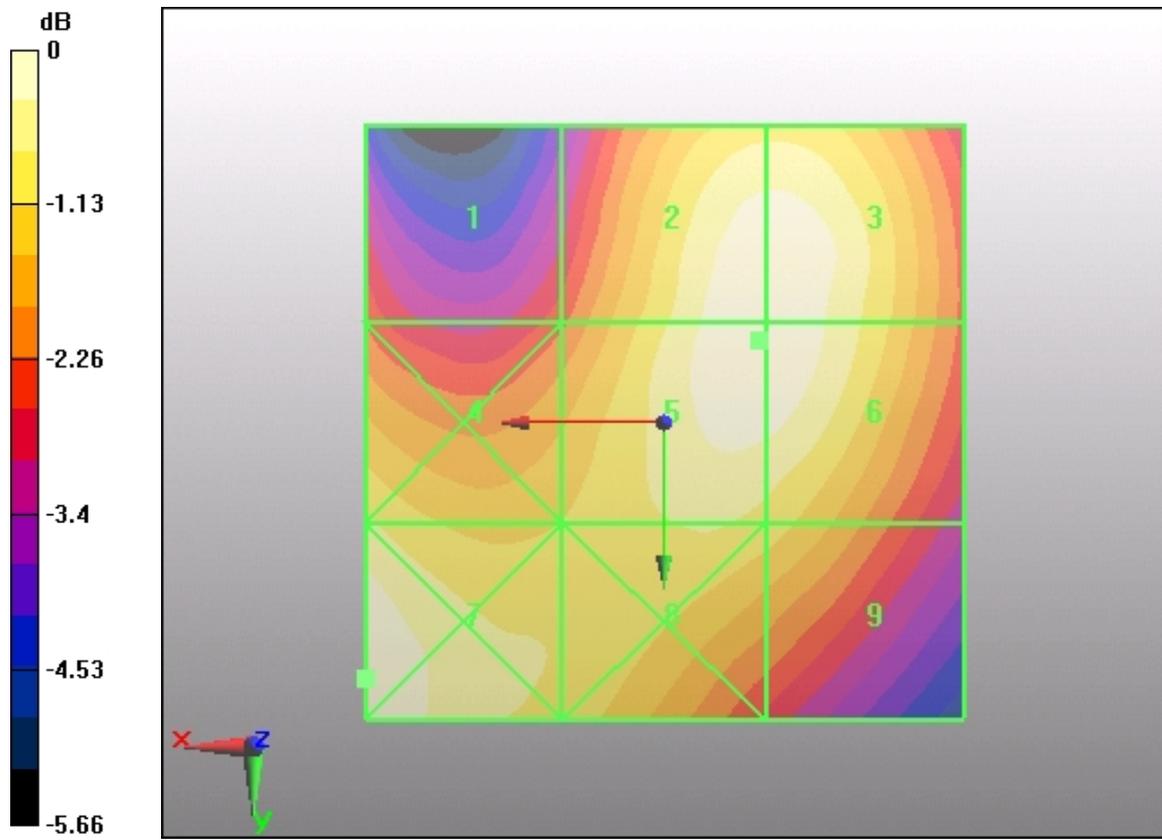
Grid 1 <b>32.1 M4</b>	Grid 2 <b>41.3 M4</b>	Grid 3 <b>41.2 M4</b>
Grid 4 <b>38.6 M4</b>	Grid 5 <b>41.3 M4</b>	Grid 6 <b>41.3 M4</b>
Grid 7 <b>41.6 M4</b>	Grid 8 <b>38.3 M4</b>	Grid 9 <b>37.4 M4</b>

**Cursor:**

Total = 41.6 V/m

E Category: M4

Location: 25, 21.5, 8.7 mm



0 dB = 41.6V/m

Test Laboratory: HUAWEI SAR Lab

**HAC\_ER3DV6\_M570-CDMA1900-25CH****DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 1851.25 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 11/11/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn852; Calibrated: 11/16/2011
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

**Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1):** Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 53.8 V/m

Probe Modulation Factor = 1.02

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 64 V/m; Power Drift = -0.087 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak E-field in V/m

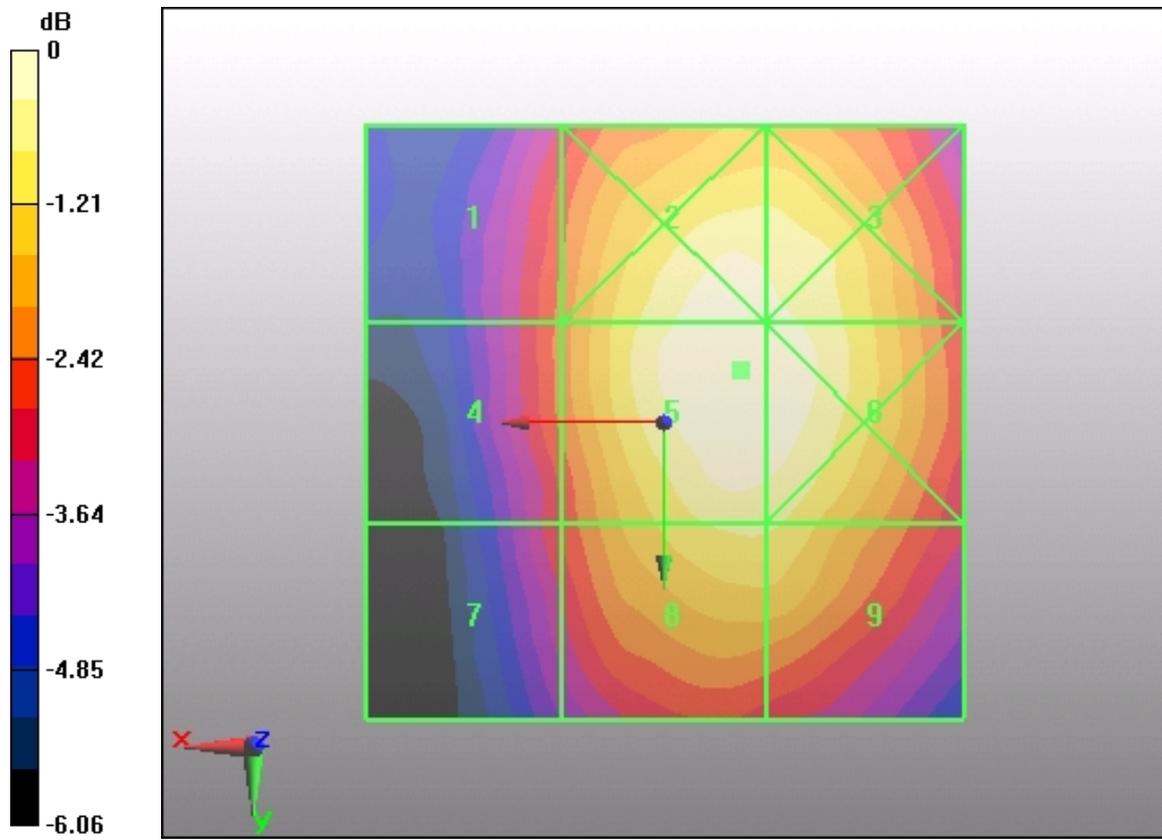
Grid 1 <b>41.6 M4</b>	Grid 2 <b>53.2 M4</b>	Grid 3 <b>52.5 M4</b>
Grid 4 <b>41.8 M4</b>	Grid 5 <b>53.8 M4</b>	Grid 6 <b>53.7 M4</b>
Grid 7 <b>39.3 M4</b>	Grid 8 <b>49.6 M4</b>	Grid 9 <b>49.5 M4</b>

**Cursor:**

Total = 53.8 V/m

E Category: M4

Location: -6.5, -4.5, 8.7 mm



0 dB = 53.8V/m

Test Laboratory: HUAWEI SAR Lab

## HAC\_ER3DV6\_M570-CDMA1900-600CH

**DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 1880 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 11/11/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn852; Calibrated: 11/16/2011
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

### Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 46.9 V/m

Probe Modulation Factor = 1.02

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 54.5 V/m; Power Drift = -0.083 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak E-field in V/m

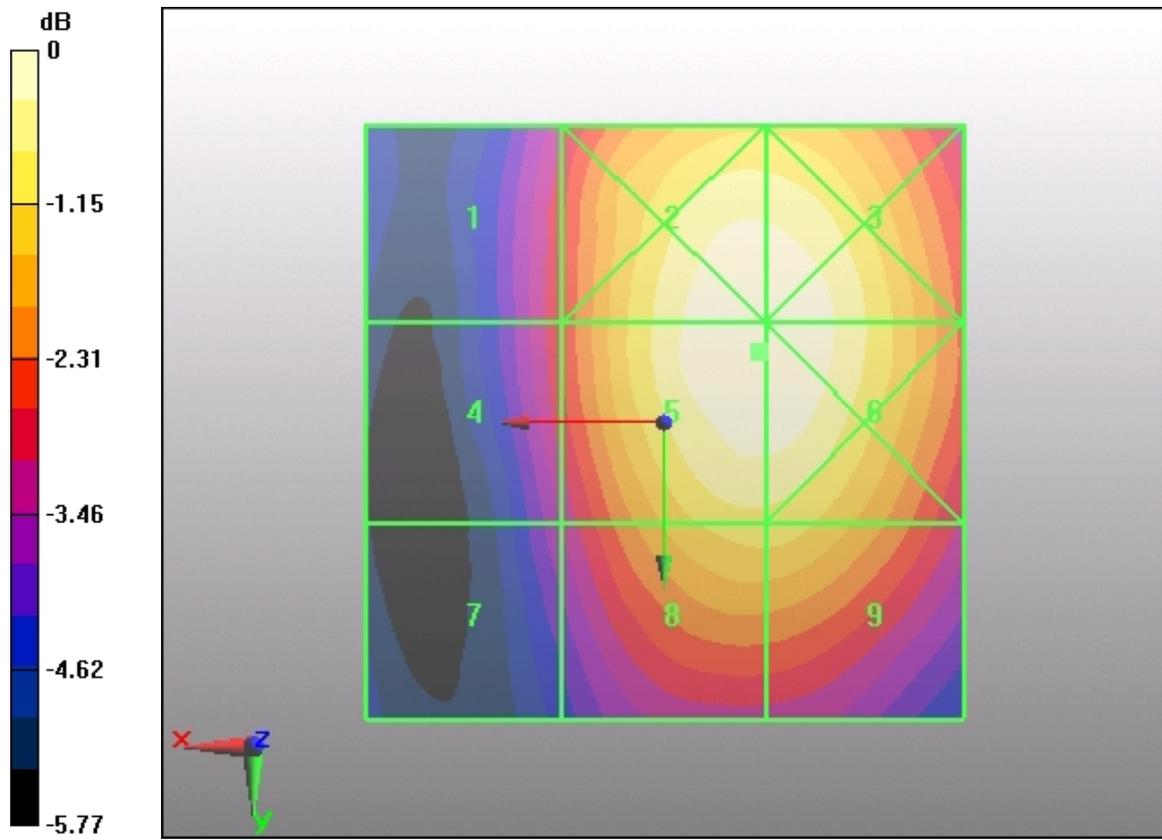
Grid 1 <b>34.6 M4</b>	Grid 2 <b>46.8 M4</b>	Grid 3 <b>46.8 M4</b>
Grid 4 <b>34.6 M4</b>	Grid 5 <b>46.9 M4</b>	Grid 6 <b>46.9 M4</b>
Grid 7 <b>31.7 M4</b>	Grid 8 <b>42.2 M4</b>	Grid 9 <b>42.2 M4</b>

#### Cursor:

Total = 46.9 V/m

E Category: M4

Location: -8, -6, 8.7 mm



0 dB = 46.9V/m

Test Laboratory: HUAWEI SAR Lab

## HAC\_ER3DV6\_M570-CDMA1900-1175CH

**DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 1908.75 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 11/11/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn852; Calibrated: 11/16/2011
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

### Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 41.1 V/m

Probe Modulation Factor = 1.02

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 44.9 V/m; Power Drift = -0.056 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak E-field in V/m

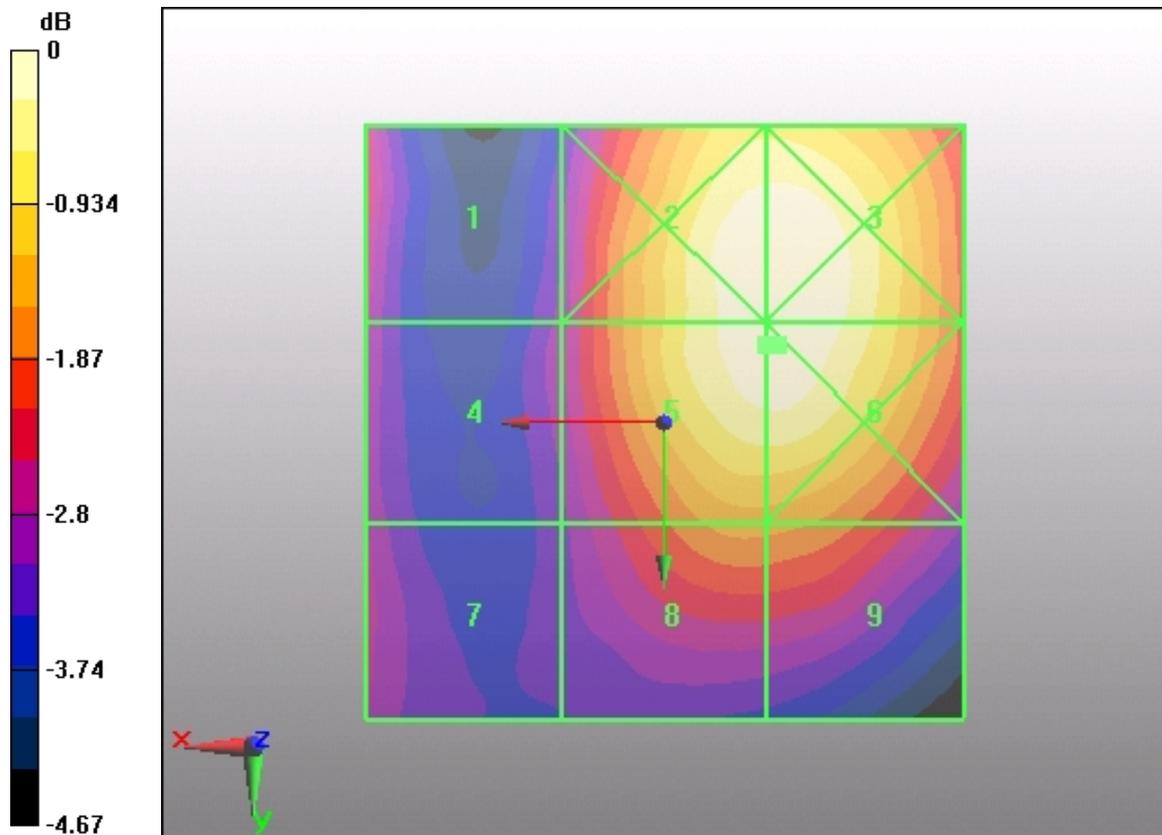
Grid 1 <b>32 M4</b>	Grid 2 <b>41.1 M4</b>	Grid 3 <b>41.1 M4</b>
Grid 4 <b>30.4 M4</b>	Grid 5 <b>41.1 M4</b>	Grid 6 <b>41.2 M4</b>
Grid 7 <b>30.5 M4</b>	Grid 8 <b>35.1 M4</b>	Grid 9 <b>35 M4</b>

#### Cursor:

Total = 41.2 V/m

E Category: M4

Location: -9.5, -6.5, 8.7 mm



0 dB = 41.2V/m

Test Laboratory: HUAWEI SAR Lab

## HAC\_H3DV6\_M570-CDMA800-1013CH

**DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 824.7 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 11/21/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn852; Calibrated: 11/16/2011
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

### Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.109 A/m

Probe Modulation Factor = 0.990

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.086 A/m; Power Drift = 0.141 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak H-field in A/m

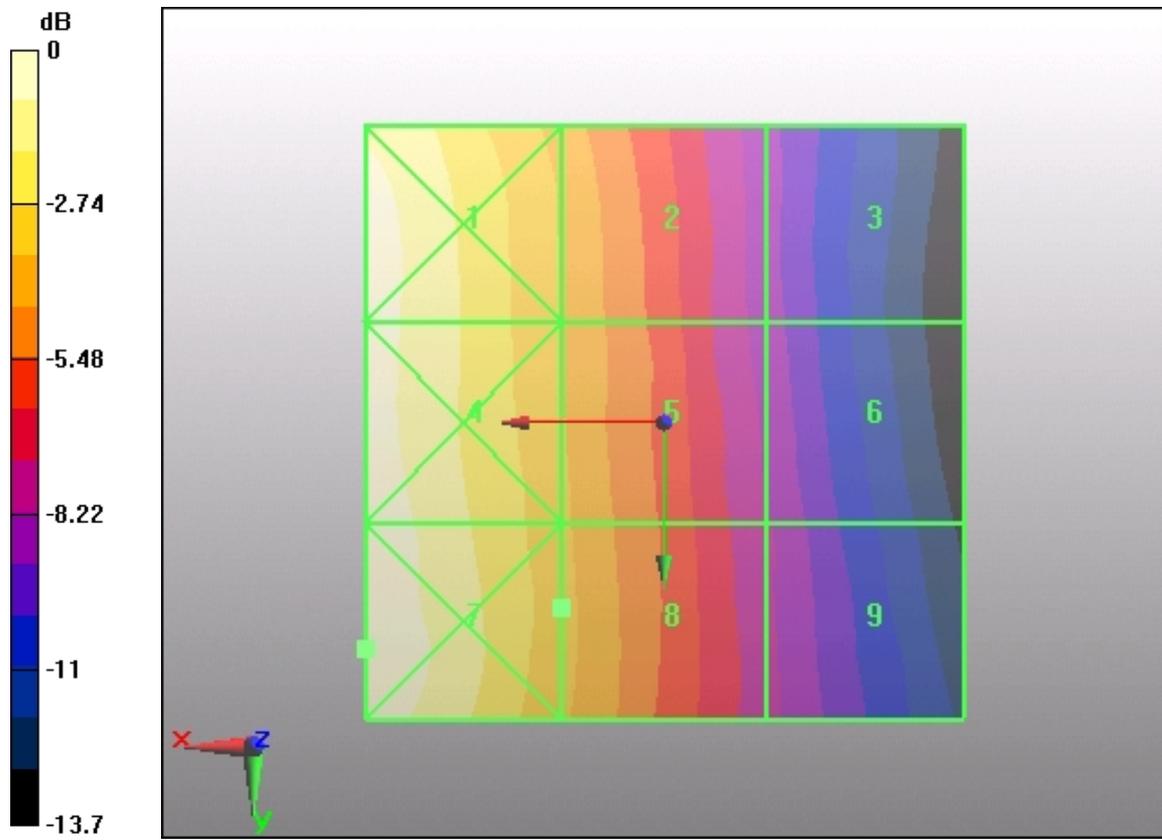
Grid 1 <b>0.153 M4</b>	Grid 2 <b>0.105 M4</b>	Grid 3 <b>0.059 M4</b>
Grid 4 <b>0.156 M4</b>	Grid 5 <b>0.108 M4</b>	Grid 6 <b>0.063 M4</b>
Grid 7 <b>0.160 M4</b>	Grid 8 <b>0.109 M4</b>	Grid 9 <b>0.065 M4</b>

**Cursor:**

Total = 0.160 A/m

H Category: M4

Location: 25, 19, 8.7 mm



0 dB = 0.160A/m

Test Laboratory: HUAWEI SAR Lab

## HAC\_H3DV6\_M570-CDMA800-384CH

**DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 836.52 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 11/21/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn852; Calibrated: 11/16/2011
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

### Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.100 A/m

Probe Modulation Factor = 0.990

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.081 A/m; Power Drift = 0.062 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak H-field in A/m

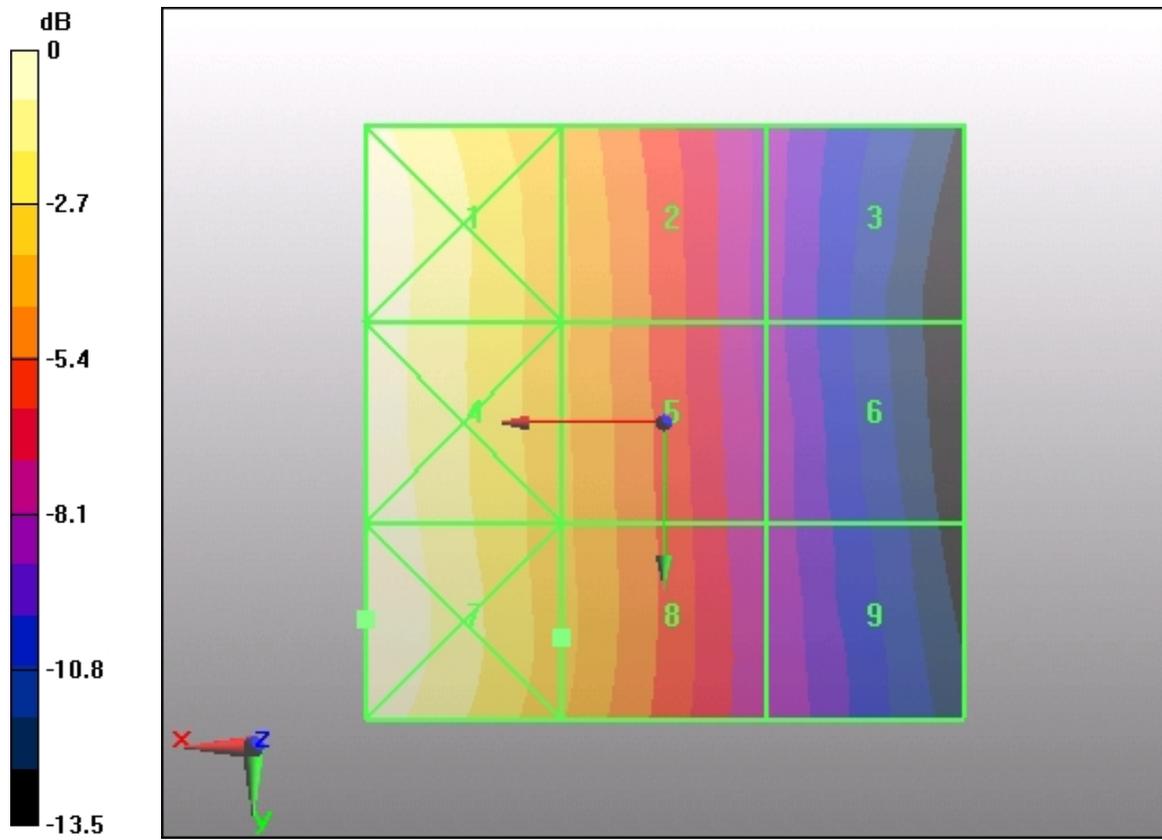
Grid 1 <b>0.142 M4</b>	Grid 2 <b>0.099 M4</b>	Grid 3 <b>0.055 M4</b>
Grid 4 <b>0.142 M4</b>	Grid 5 <b>0.099 M4</b>	Grid 6 <b>0.057 M4</b>
Grid 7 <b>0.146 M4</b>	Grid 8 <b>0.100 M4</b>	Grid 9 <b>0.058 M4</b>

**Cursor:**

Total = 0.146 A/m

H Category: M4

Location: 25, 16.5, 8.7 mm



0 dB = 0.146A/m

Test Laboratory: HUAWEI SAR Lab

**HAC\_H3DV6\_M570-CDMA800-777CH****DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 848.31 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 11/21/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn852; Calibrated: 11/16/2011
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

**Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1):** Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.119 A/m

Probe Modulation Factor = 0.990

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.098 A/m; Power Drift = -0.152 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak H-field in A/m

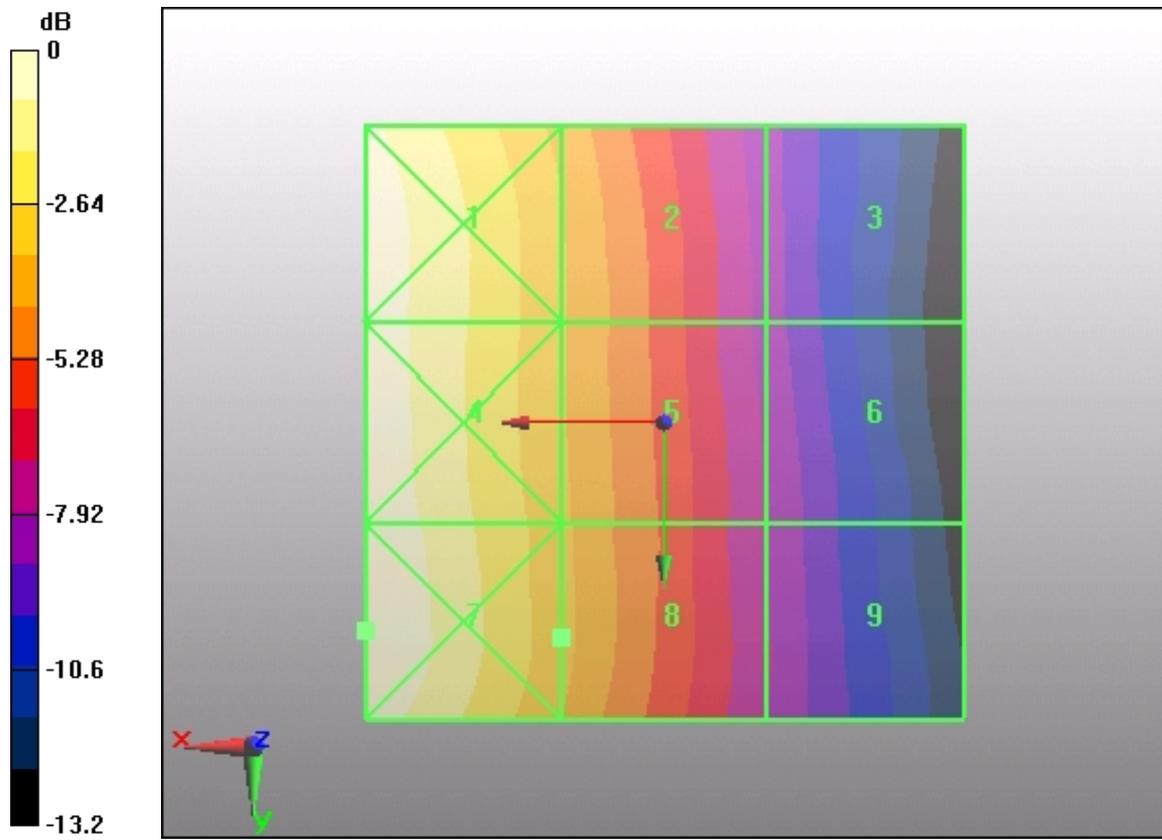
Grid 1 <b>0.168 M4</b>	Grid 2 <b>0.117 M4</b>	Grid 3 <b>0.067 M4</b>
Grid 4 <b>0.170 M4</b>	Grid 5 <b>0.118 M4</b>	Grid 6 <b>0.070 M4</b>
Grid 7 <b>0.173 M4</b>	Grid 8 <b>0.119 M4</b>	Grid 9 <b>0.071 M4</b>

**Cursor:**

Total = 0.173 A/m

H Category: M4

Location: 25, 17.5, 8.7 mm



0 dB = 0.173A/m

Test Laboratory: HUAWEI SAR Lab

## HAC\_H3DV6\_M570-CDMA1700-25CH

**DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 1711.25 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 11/21/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn852; Calibrated: 11/16/2011
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

### Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.139 A/m

Probe Modulation Factor = 0.940

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.144 A/m; Power Drift = -0.161 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak H-field in A/m

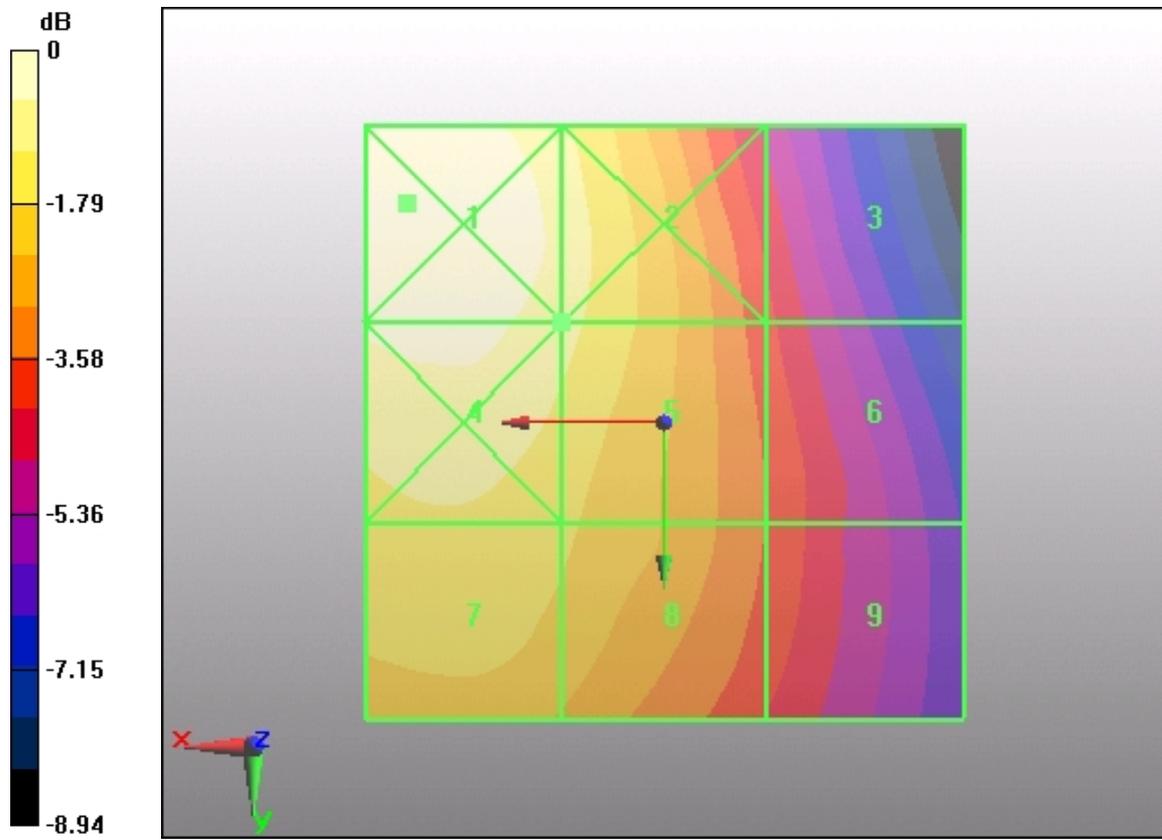
Grid 1 <b>0.155 M4</b>	Grid 2 <b>0.141 M4</b>	Grid 3 <b>0.098 M4</b>
Grid 4 <b>0.149 M4</b>	Grid 5 <b>0.139 M4</b>	Grid 6 <b>0.103 M4</b>
Grid 7 <b>0.134 M4</b>	Grid 8 <b>0.128 M4</b>	Grid 9 <b>0.103 M4</b>

#### Cursor:

Total = 0.155 A/m

H Category: M4

Location: 21.5, -18.5, 8.7 mm



0 dB = 0.155A/m

Test Laboratory: HUAWEI SAR Lab

## HAC\_H3DV6\_M570-CDMA1700-450CH

**DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 1732.5 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 11/21/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn1236; Calibrated: 3/28/2012
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

### Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.126 A/m

Probe Modulation Factor = 0.940

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.115 A/m; Power Drift = -0.00117 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak H-field in A/m

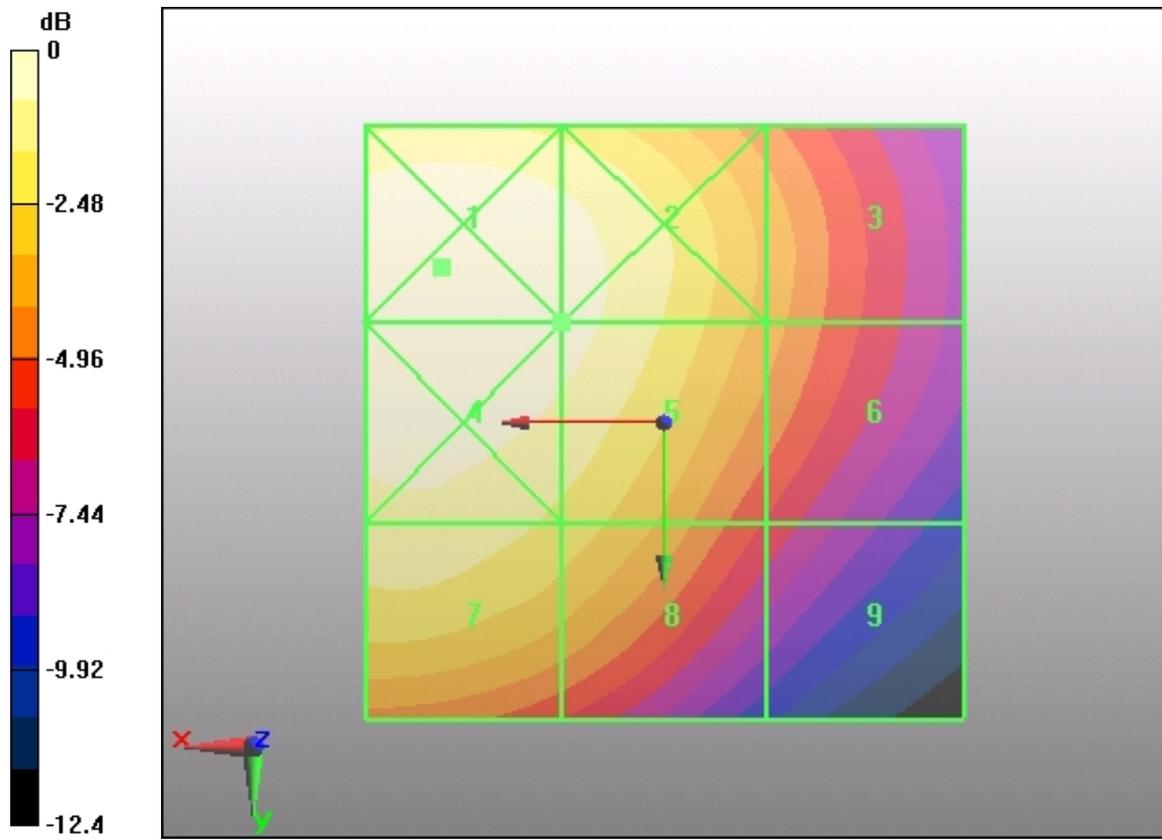
Grid 1 <b>0.134 M4</b>	Grid 2 <b>0.128 M4</b>	Grid 3 <b>0.090 M4</b>
Grid 4 <b>0.133 M4</b>	Grid 5 <b>0.126 M4</b>	Grid 6 <b>0.088 M4</b>
Grid 7 <b>0.118 M4</b>	Grid 8 <b>0.107 M4</b>	Grid 9 <b>0.068 M4</b>

#### Cursor:

Total = 0.134 A/m

H Category: M4

Location: 18.5, -13, 8.7 mm



0 dB = 0.134A/m

Test Laboratory: HUAWEI SAR Lab

## HAC\_H3DV6\_M570-CDMA1700-850CH

**DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 1752.5 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 11/21/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn852; Calibrated: 11/16/2011
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

### Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.126 A/m

Probe Modulation Factor = 0.940

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.132 A/m; Power Drift = -0.039 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak H-field in A/m

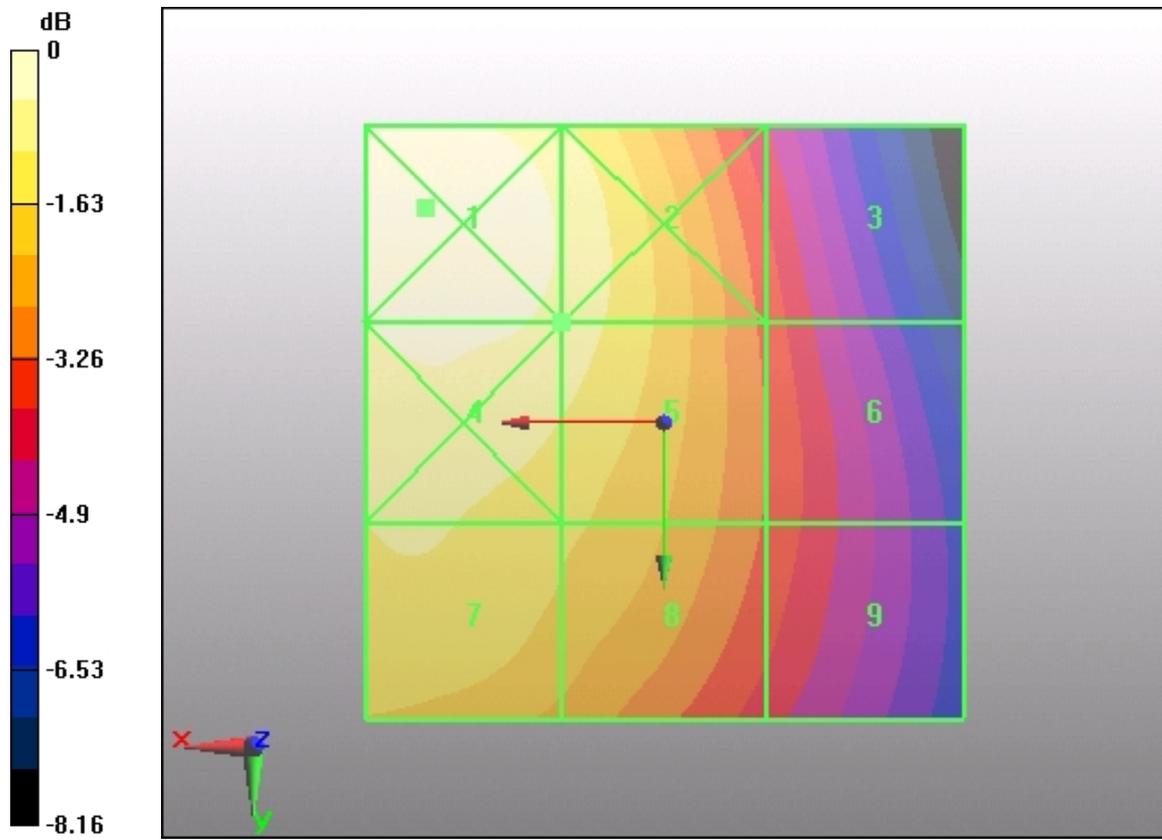
Grid 1 <b>0.137 M4</b>	Grid 2 <b>0.128 M4</b>	Grid 3 <b>0.093 M4</b>
Grid 4 <b>0.132 M4</b>	Grid 5 <b>0.126 M4</b>	Grid 6 <b>0.095 M4</b>
Grid 7 <b>0.122 M4</b>	Grid 8 <b>0.115 M4</b>	Grid 9 <b>0.094 M4</b>

#### Cursor:

Total = 0.137 A/m

H Category: M4

Location: 20, -18, 8.7 mm



0 dB = 0.137A/m

Test Laboratory: HUAWEI SAR Lab

**HAC\_H3DV6\_M570-CDMA1900-25CH****DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 1851.25 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 11/21/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn852; Calibrated: 11/16/2011
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

**Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1):** Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.130 A/m

Probe Modulation Factor = 0.940

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.122 A/m; Power Drift = 0.017 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak H-field in A/m

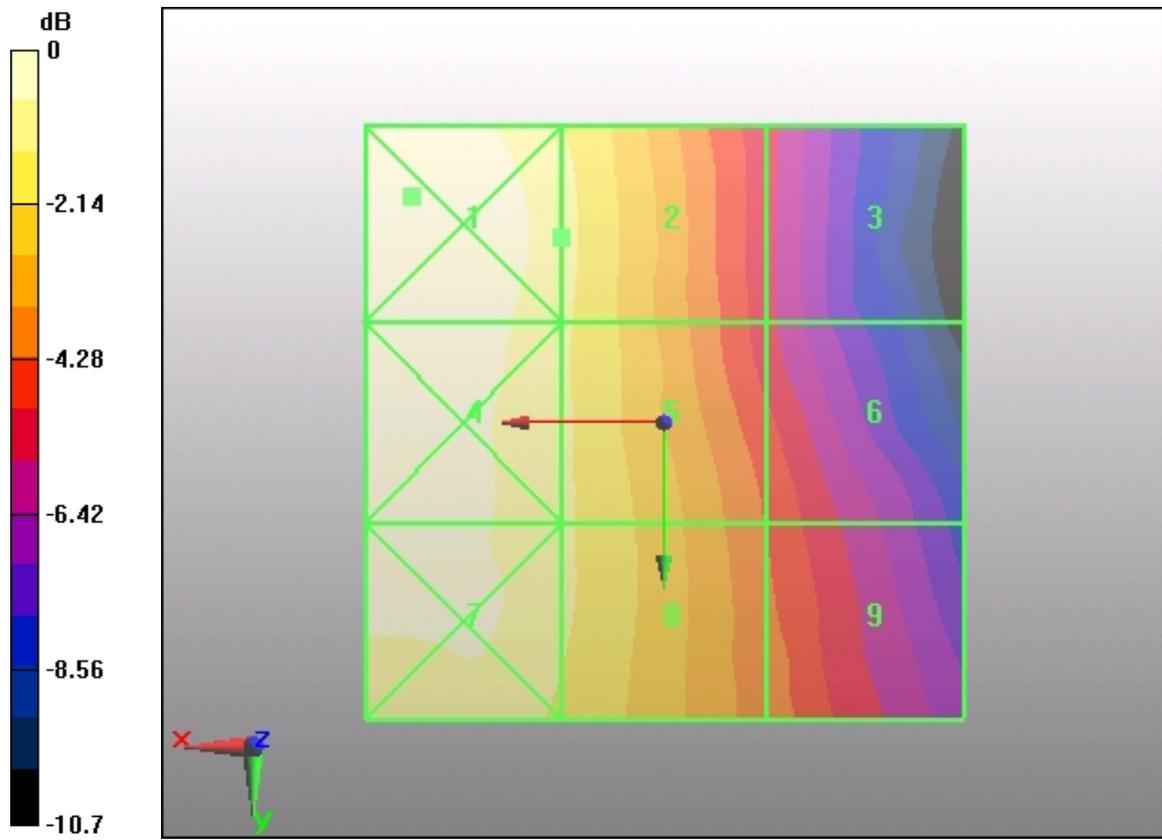
Grid 1 <b>0.148 M4</b>	Grid 2 <b>0.130 M4</b>	Grid 3 <b>0.080 M4</b>
Grid 4 <b>0.146 M4</b>	Grid 5 <b>0.128 M4</b>	Grid 6 <b>0.090 M4</b>
Grid 7 <b>0.140 M4</b>	Grid 8 <b>0.128 M4</b>	Grid 9 <b>0.095 M4</b>

**Cursor:**

Total = 0.148 A/m

H Category: M4

Location: 21, -19, 8.7 mm



0 dB = 0.148A/m

Test Laboratory: HUAWEI SAR Lab

## HAC\_H3DV6\_M570-CDMA1900-600CH

**DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 1880 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 11/21/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn852; Calibrated: 11/16/2011
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

### Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.123 A/m

Probe Modulation Factor = 0.940

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.123 A/m; Power Drift = -0.00542 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak H-field in A/m

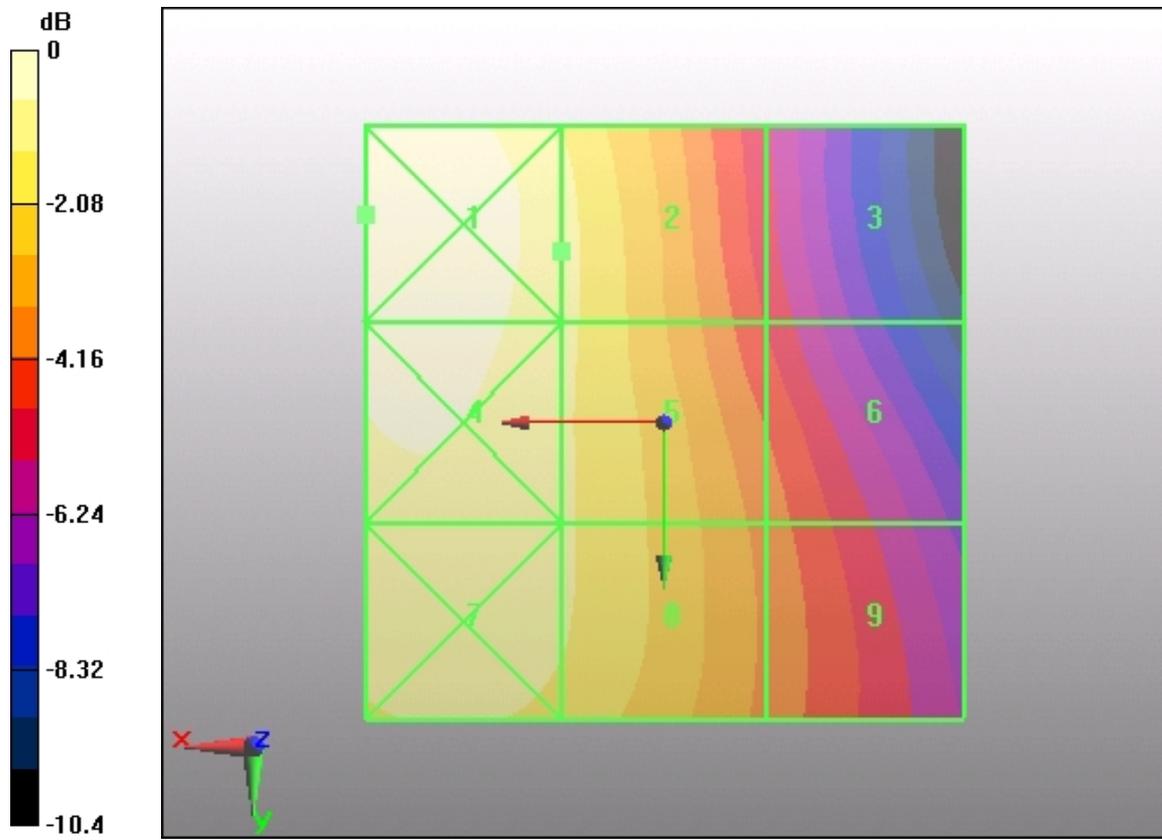
Grid 1 <b>0.140 M4</b>	Grid 2 <b>0.123 M4</b>	Grid 3 <b>0.080 M4</b>
Grid 4 <b>0.135 M4</b>	Grid 5 <b>0.122 M4</b>	Grid 6 <b>0.091 M4</b>
Grid 7 <b>0.128 M4</b>	Grid 8 <b>0.121 M4</b>	Grid 9 <b>0.093 M4</b>

**Cursor:**

Total = 0.140 A/m

H Category: M4

Location: 25, -17.5, 8.7 mm



0 dB = 0.140A/m

Test Laboratory: HUAWEI SAR Lab

**HAC\_H3DV6\_M650-CDMA1900-1175CH****DUT: M570; Type: CDMA 1X Mobile Phone; Serial: SAR1**

Communication System: HW -CDMA2000; Frequency: 1908.75 MHz

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 1$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY5 Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 11/21/2011
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn852; Calibrated: 11/16/2011
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA
- Measurement SW: DASY52, V52.8 Build 1; SEMCAD X Version 14.0 Build 57

**Device H-Field measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1):** Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.121 A/m

Probe Modulation Factor = 0.940

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.123 A/m; Power Drift = 0.030 dB

**Hearing Aid Near-Field Category: M4 (AWF 0 dB)**

Peak H-field in A/m

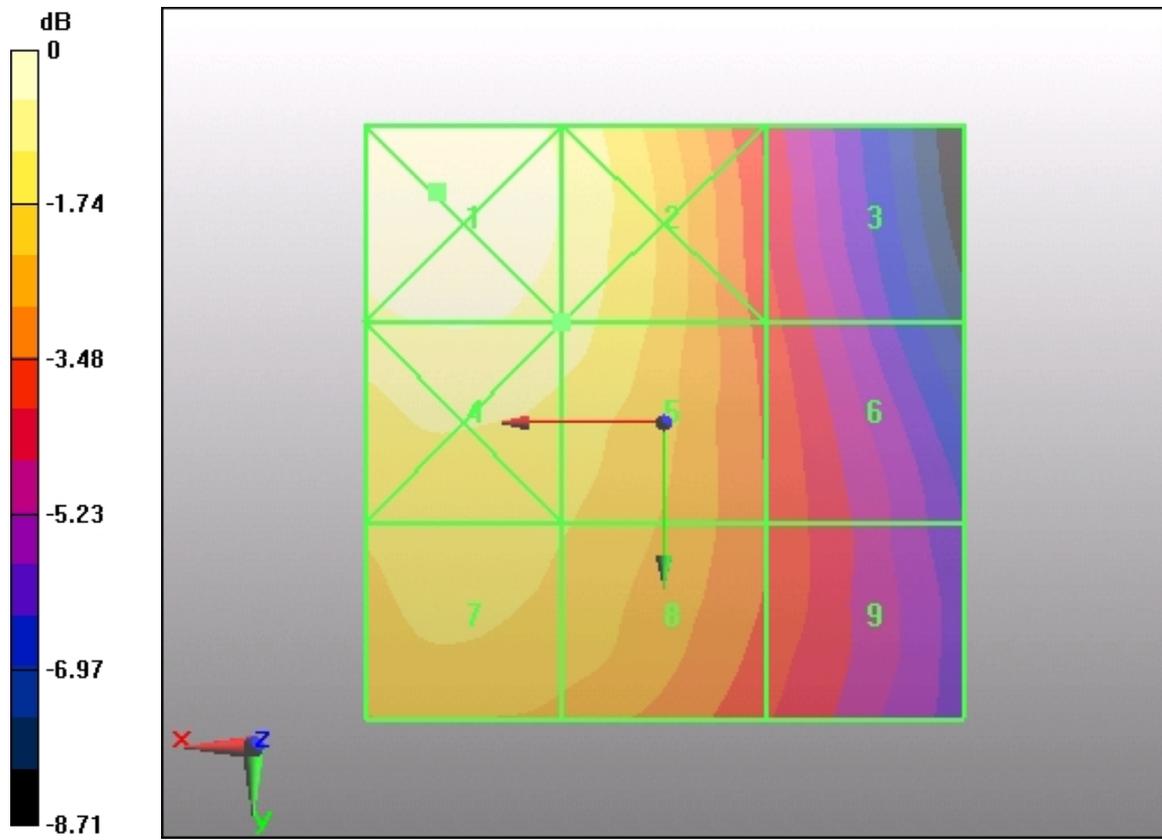
Grid 1 <b>0.134 M4</b>	Grid 2 <b>0.125 M4</b>	Grid 3 <b>0.087 M4</b>
Grid 4 <b>0.126 M4</b>	Grid 5 <b>0.121 M4</b>	Grid 6 <b>0.090 M4</b>
Grid 7 <b>0.113 M4</b>	Grid 8 <b>0.110 M4</b>	Grid 9 <b>0.090 M4</b>

**Cursor:**

Total = 0.134 A/m

H Category: M4

Location: 19, -19.5, 8.7 mm



0 dB = 0.134A/m